# Very Low Forward Voltage Trench-based Schottky Rectifier

Exceptionally Low  $V_F = 0.42$  V at  $I_F = 5$  A

## Features

- Fine Lithography Trench–based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- Pb-Free and Halide-Free Packages are Available

## **Typical Applications**

- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

## **Mechanical Characteristics**

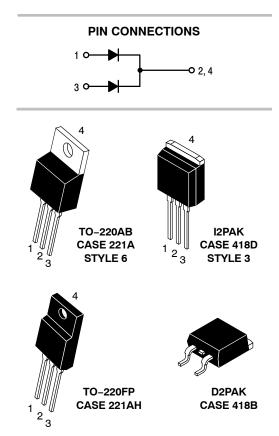
- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec



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VERY LOW FORWARD VOLT-AGE, LOW LEAKAGE SCHOT-TKY BARRIER RECTIFIERS 30 AMPERES, 100 VOLTS



## ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

### MAXIMUM RATINGS

Rating			Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	100	V
Average Rectified Forward Current (Rated $V_R$ , $T_C$ = 125°C)	Per device Per diode	I <sub>F(AV)</sub>	30 15	A
Peak Repetitive Forward Current (Rated V <sub>R</sub> , Square Wave, 20 kHz, T <sub>C</sub> = 120°C)	Per device Per diode	I <sub>FRM</sub>	60 30	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)		I <sub>FSM</sub>	160	A
Operating Junction Temperature		TJ	-40 to +150	°C
Storage Temperature		T <sub>stg</sub>	-40 to +150	°C
Voltage Rate of Change (Rated V <sub>R</sub> )		dv/dt	10,000	V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

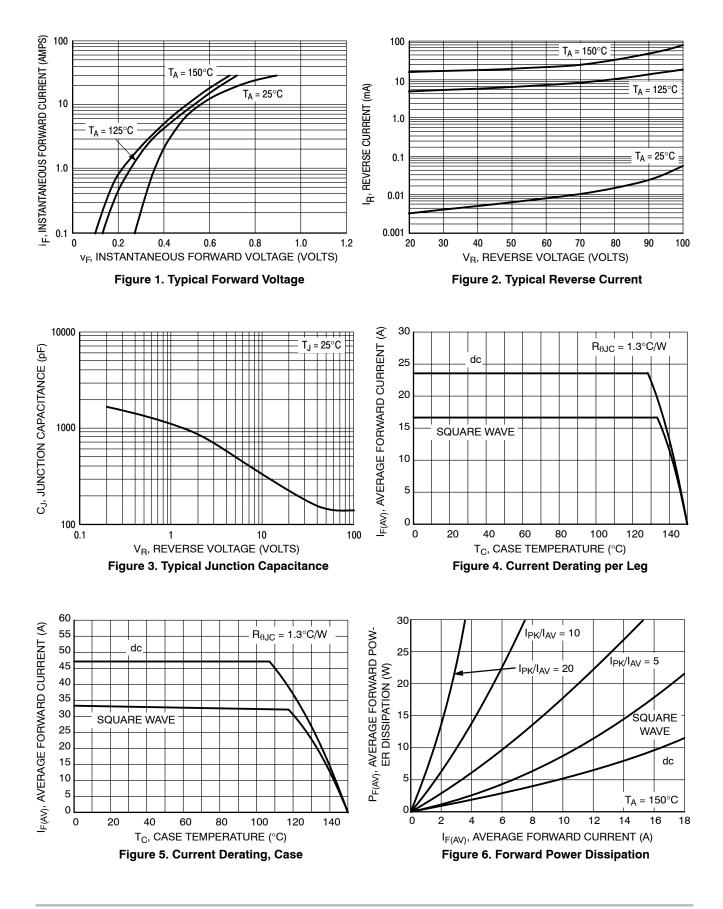
### THERMAL CHARACTERISTICS

Rating	Symbol	NTST30U100CTG, NTSB30U100CT-1G	NTSB30U100CTG	NTSJ30U100CTG	Unit
Maximum Thermal Resistance per Diode Junction-to-Case Junction-to-Ambient	$R_{ heta JC} \ R_{ heta JA}$	2.5 70	0.93 46.5	3.81 105	°C/W °C/W

#### ELECTRICAL CHARACTERISTICS (Per Leg unless otherwise noted)

Rating	Symbol	Тур	Max	Unit
Maximum Instantaneous Forward Voltage (Note 1)	VF	0.47 0.52 0.66	_ _ 0.80	V
$(I_F = 5 \text{ A}, T_J = 125^{\circ}\text{C})$ $(I_F = 7.5 \text{ A}, T_J = 125^{\circ}\text{C})$ $(I_F = 15 \text{ A}, T_J = 125^{\circ}\text{C})$		0.42 0.48 0.60	_ _ 0.65	
Maximum Instantaneous Reverse Current (Note 1) $(V_R = 70 \text{ V}, T_J = 25^{\circ}\text{C})$ $(V_R = 70 \text{ V}, T_J = 125^{\circ}\text{C})$	I <sub>R</sub>	15 12		μA mA
(Rated dc Voltage, $T_J = 25^{\circ}C$ ) (Rated dc Voltage, $T_J = 125^{\circ}C$ )		65 32	675 60	μA mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 1. Pulse Test: Pulse Width =  $300 \ \mu$ s, Duty Cycle  $\leq 2.0\%$ 



## **TYPICAL CHARACTERISITICS**

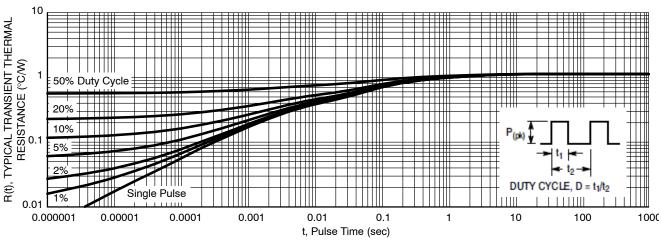


Figure 7. Typical Transient Thermal Response, Junction-to-Case for NTST30U100CT and NTSB30U100CT-1G

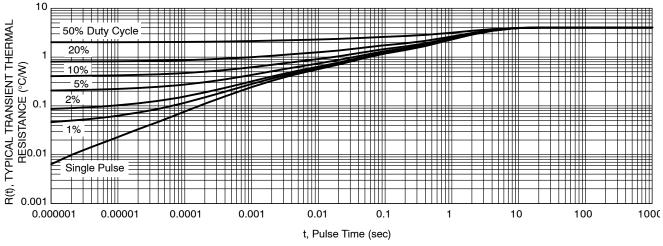
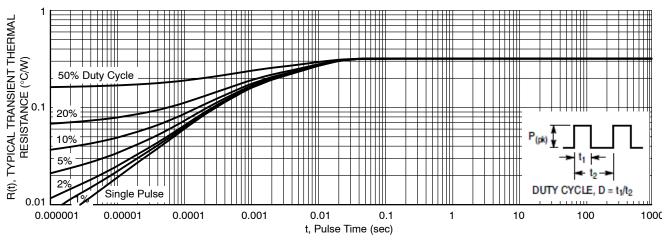


Figure 8. Typical Transient Thermal Response, Junction-to-Case for NTSJ30U100CTG



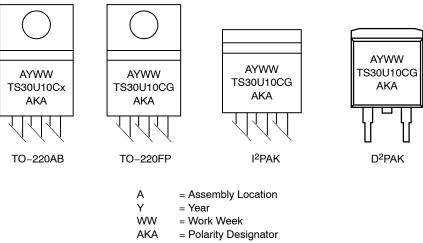


**TYPICAL CHARACTERISITICS** 

### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>	
NTST30U100CTG	TO-220AB (Pb-Free)	50 Units / Rail	
NTST30U100CTH	TO-220AB (Halide-Free)	50 Units / Rail	
NTSB30U100CT-1G	I <sup>2</sup> PAK (Pb-Free)	50 Units / Rail	
NTSJ30U100CTG	TO-220FP (Halide-Free)	50 Units / Rail	
NTSB30U100CTG	D <sup>2</sup> PAK (Pb-Free)	50 Units / Rail	
NTSB30U100CTT4G	D <sup>2</sup> PAK (Pb–Free)	800 / Tape & Reel	

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

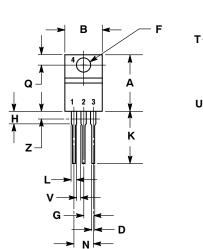


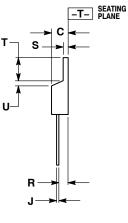
#### **MARKING DIAGRAMS**

- х
- = G or H
- = Pb-Free Package G н
- = Halide-Free Package

### PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AH** 

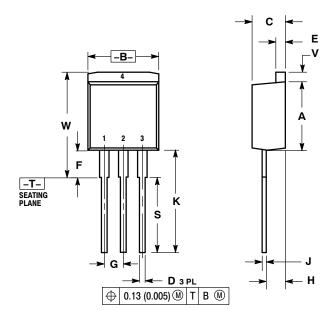




NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.570	0.620	14.48	15.75	
В	0.380	0.415	9.66	10.53	
С	0.160	0.190	4.07	4.83	
D	0.025	0.038	0.64	0.96	
F	0.142	0.161	3.61	4.09	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.161	2.80	4.10	
J	0.014	0.024	0.36	0.61	
Κ	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
Ν	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.39	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
۷	0.045		1.15		
Ζ		0.080		2.04	
STYLE 6: PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE					

I<sup>2</sup>PAK (TO-262) CASE 418D **ISSUE D** 

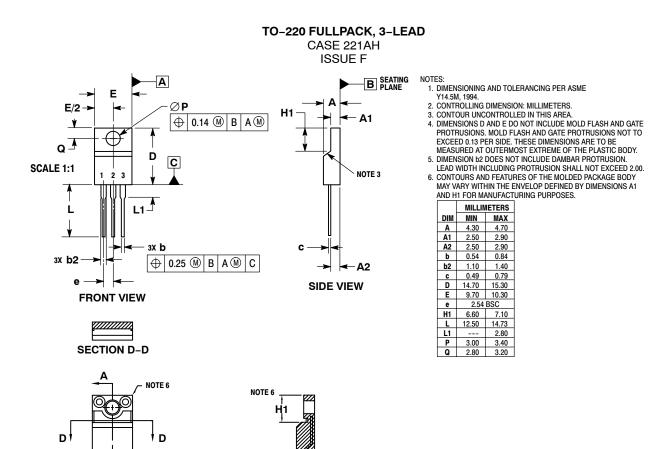


NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.335	0.380	8.51	9.65
В	0.380	0.406	9.65	10.31
С	0.160	0.185	4.06	4.70
D	0.026	0.035	0.66	0.89
Е	0.045	0.055	1.14	1.40
F	0.122 REF		3.10 REF	
G	0.100 BSC		2.54 BSC	
Н	0.094	0.110	2.39	2.79
J	0.013	0.025	0.33	0.64
Κ	0.500	0.562	12.70	14.27
S	0.390 REF		9.90 REF	
V	0.045	0.070	1.14	1.78
W	0.522	0.551	13.25	14.00

STYLE 3: PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE

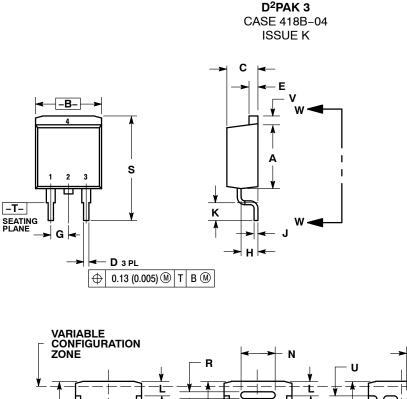
## PACKAGE DIMENSIONS



**SECTION A-A** 

A ALTERNATE CONSTRUCTION

#### PACKAGE DIMENSIONS

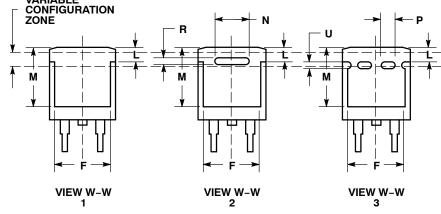


NOTES:

 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 CONTROLLING DIMENSION: INCH.
418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

	INCHES		MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.340	0.380	8.64	9.65	
В	0.380	0.405	9.65	10.29	
С	0.160	0.190	4.06	4.83	
D	0.020	0.035	0.51	0.89	
ш	0.045	0.055	1.14	1.40	
F	0.310	0.350	7.87	8.89	
G	0.100	BSC	2.54	4 BSC	
Н	0.080	0.110	2.03	2.79	
ſ	0.018	0.025	0.46	0.64	
κ	0.090	0.110	2.29	2.79	
L	0.052	0.072	1.32	1.83	
Μ	0.280	0.320	7.11	8.13	
Ν	0.197 REF		5.00 REF		
Ρ	0.079	0.079 REF		REF	
R	0.039	REF	0.99	REF	
s	0.575	0.625	14.60	15.88	
v	0.045	0.055	1.14	1.40	



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#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

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